

## GSMBTA64

### PNP SILICON TRANSISTOR

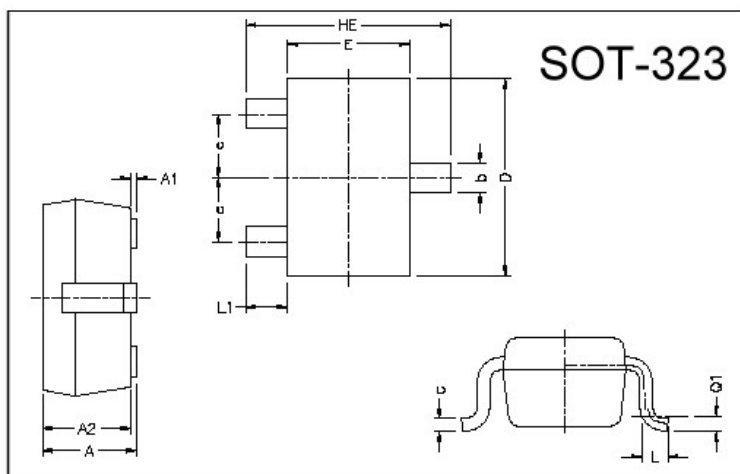
#### Description

The GSMBTA64 is designed for application requiring extremely high current gain at collector to 500mA.

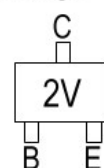
#### Features

- High D.C. Current Gain
- Complementary to GSMBTA14

#### Package Dimensions



Marking :



| REF. | Millimeter |      | REF. | Millimeter |      |
|------|------------|------|------|------------|------|
|      | Min.       | Max. |      | Min.       | Max. |
| A    | 0.80       | 1.10 | L1   | 0.42 REF.  |      |
| A1   | 0          | 0.10 | L    | 0.15       | 0.35 |
| A2   | 0.80       | 1.00 | b    | 0.25       | 0.40 |
| D    | 1.80       | 2.20 | c    | 0.10       | 0.25 |
| E    | 1.15       | 1.35 | e    | 0.65 REF.  |      |
| HE   | 1.80       | 2.40 | Q1   | 0.15 BSC.  |      |

#### Absolute Maximum Ratings at Ta = 25°C

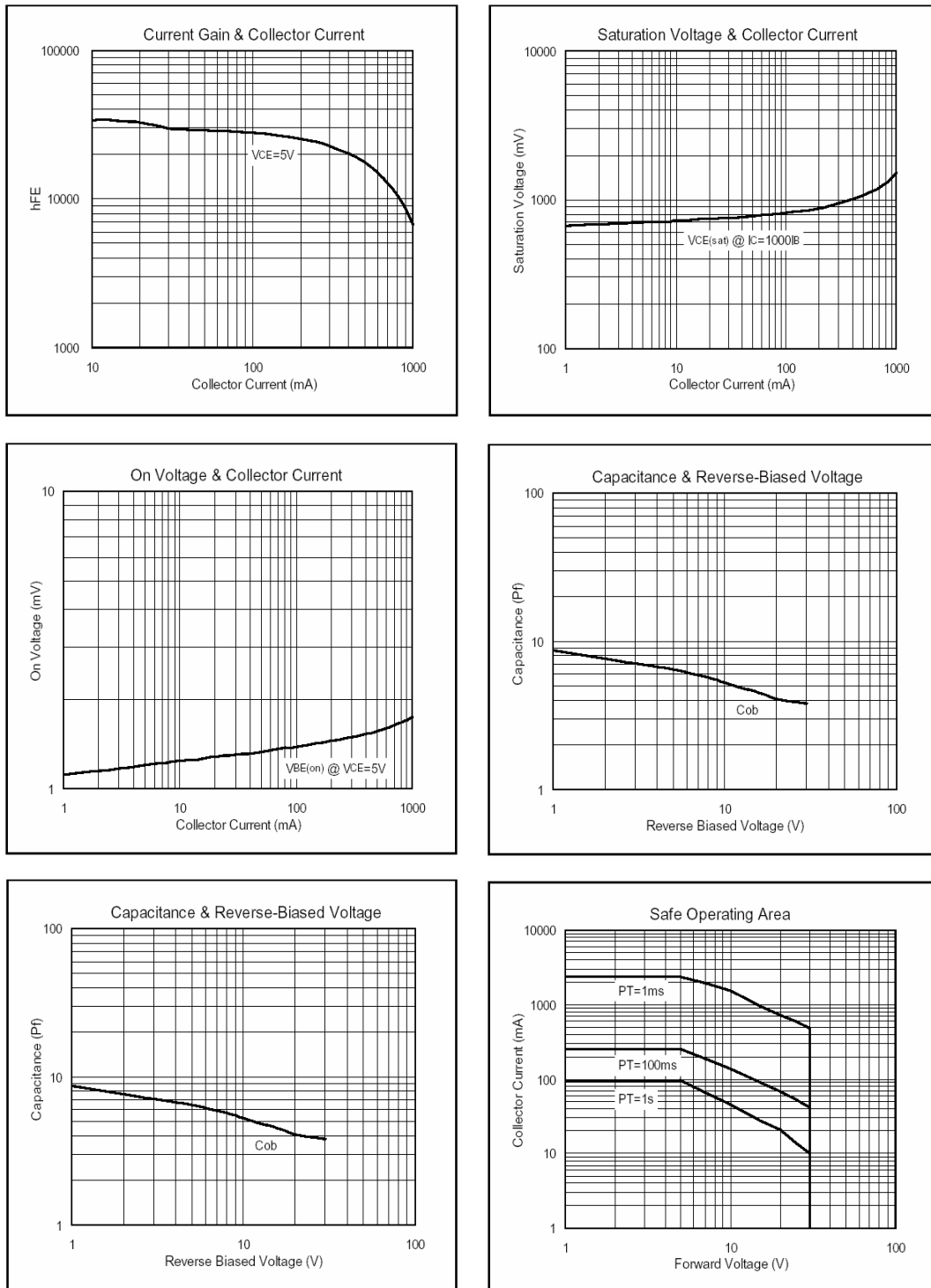
| Parameter                    | Symbol | Ratings  | Unit |
|------------------------------|--------|----------|------|
| Junction Temperature         | Tj     | +150     | °C   |
| Storage Temperature          | Tstg   | -55~+150 | °C   |
| Collector to Base Voltage    | VCBO   | -30      | V    |
| Collector to Emitter Voltage | VCEO   | -30      | V    |
| Emitter to Base Voltage      | VEBO   | -10      | V    |
| Collector Current            | IC     | -500     | mA   |
| Total Power Dissipation      | PD     | 225      | mW   |

#### Electrical Characteristics (Ta = 25°C, unless otherwise noted)

| Symbol    | Min. | Typ. | Max. | Unit | Test Conditions              |
|-----------|------|------|------|------|------------------------------|
| BVCBO     | -30  | -    | -    | V    | IC=-100uA, IE=0              |
| BVCEO     | -30  | -    | -    | V    | IC=-100uA, IB=0              |
| BVEBO     | -10  | -    | -    | V    | IE=-10uA, IC=0               |
| ICBO      | -    | -    | -100 | nA   | VCB=-30V, IE=0               |
| IEBO      | -    | -    | -100 | nA   | VEB=-10V, IC=0               |
| *VCE(sat) | -    | -    | -1.5 | V    | IC=-100mA, IB=-0.1mA         |
| *VBE(on)  | -    | -    | -2   | V    | VCE=-5V, IC=-100mA           |
| *hFE1     | 10K  | -    | -    |      | VCE=-5V, IC=-10mA            |
| *hFE2     | 20K  | -    | -    |      | VCE=-5V, IC=-100mA           |
| fT        | 125  | -    | -    | MHz  | VCE=-5V, IC=-100mA, f=100MHz |

\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

## Characteristics Curve



### Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

### Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165